FAIRCHILD
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# IRF9530, RF1S9530SM

**Data Sheet** January 2002

## 12A, 100V, 0.300 Ohm, P-Channel Power MOSFETs

These are P-Channel enhancement mode silicon gate power field effect transistors. They are advanced power MOSFETs designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. All of these power MOSFETs are designed for applications such as switching regulators, switching convertors, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. The high input impedance allows these types to be operated directly from integrated circuits.

Formerly developmental type TA17511.

## Ordering Information

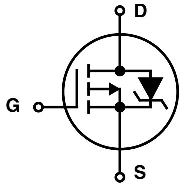
| PART NUMBER | PACKAGE | BRAND |
|---|---|---|
| IRF9530 | TO-220AB | IRF9530 |
| RF1S9530SM | TO-263AB | RF1S9530 |

NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-263AB variant in the tape and reel, i.e., RF1S9530SM9A.

## Features

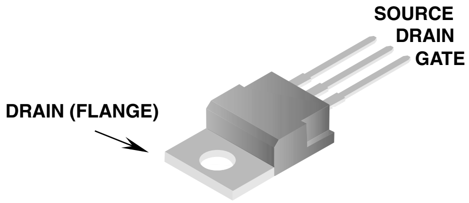
- 12A, 100V
- $r_{DS(ON)} = 0.300\Omega$
- Single Pulse Avalanche Energy Rated
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Related Literature
  - TB334, “Guidelines for Soldering Surface Mount Components to PC Boards”

## Symbol



## Packaging

**JEDEC TO-220AB**



**JEDEC TO-263A**